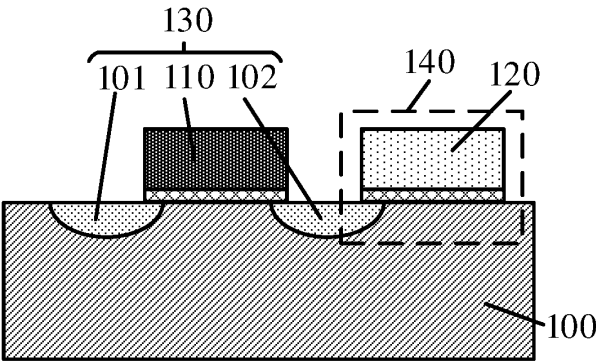
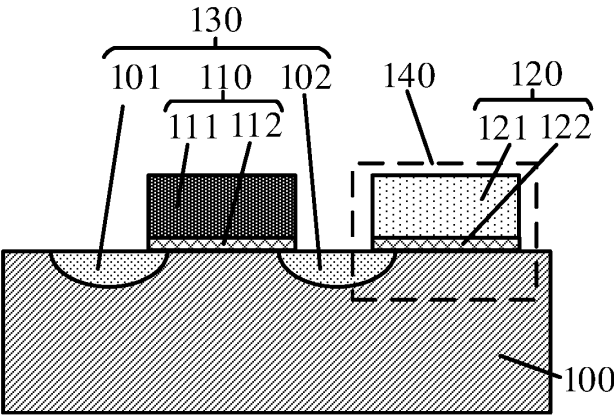




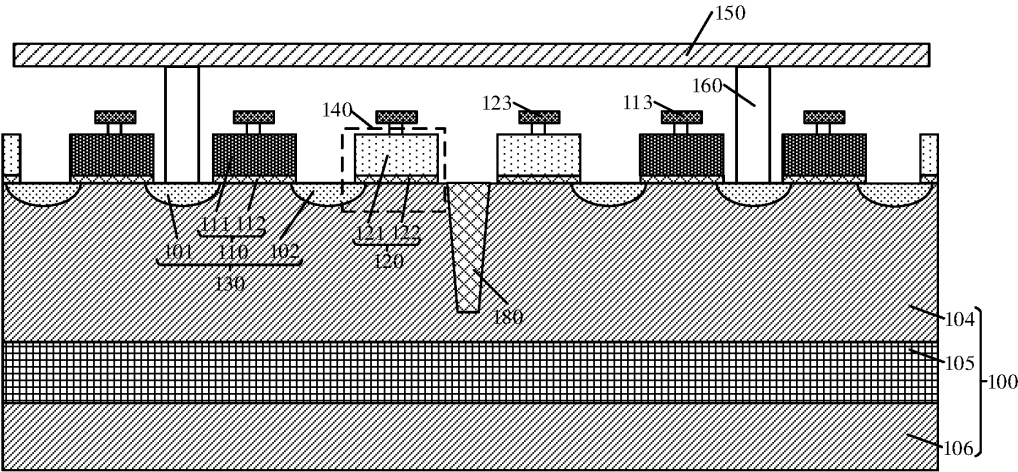
10

图 1

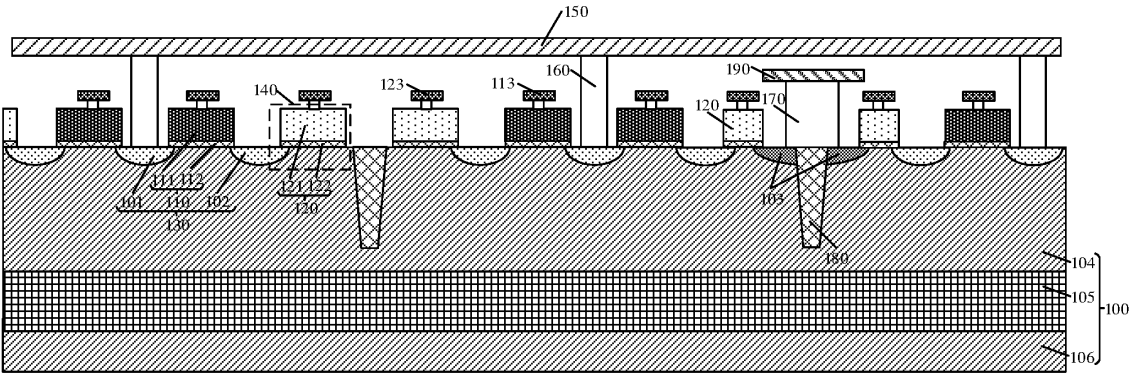


10

图 2



10
图 3



10
图 4

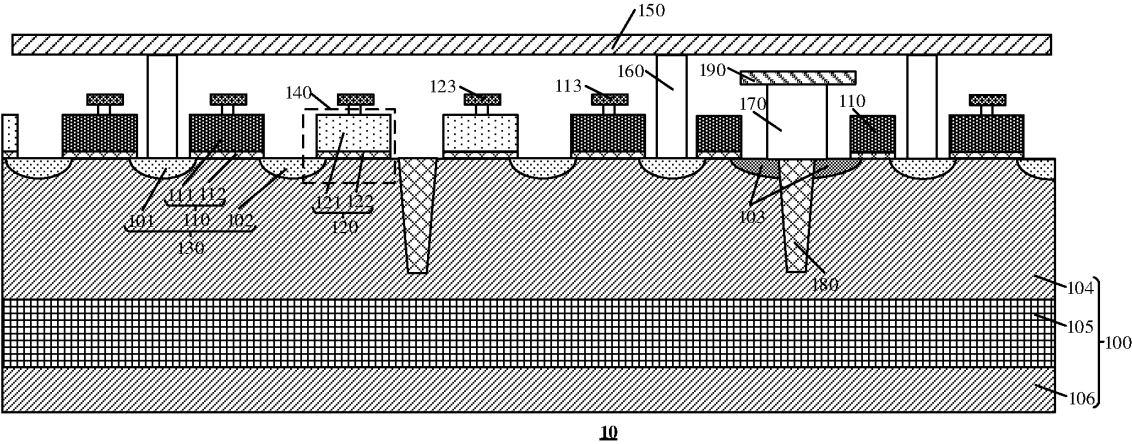


图 5

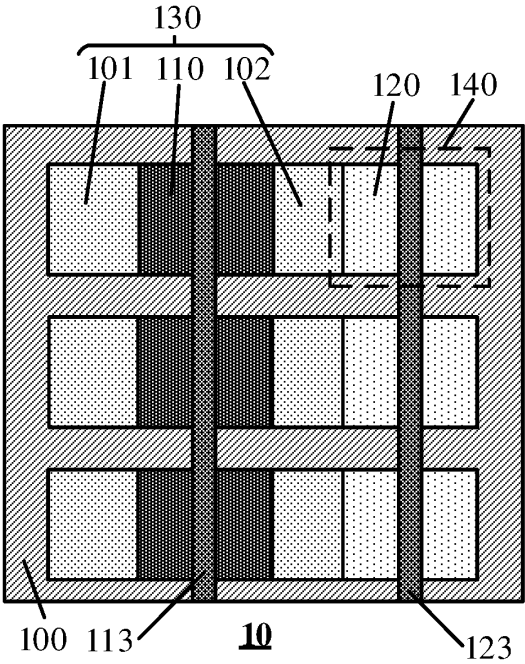


图 6

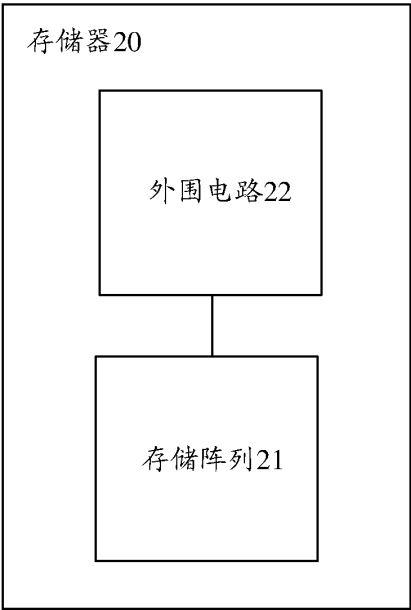


图 7

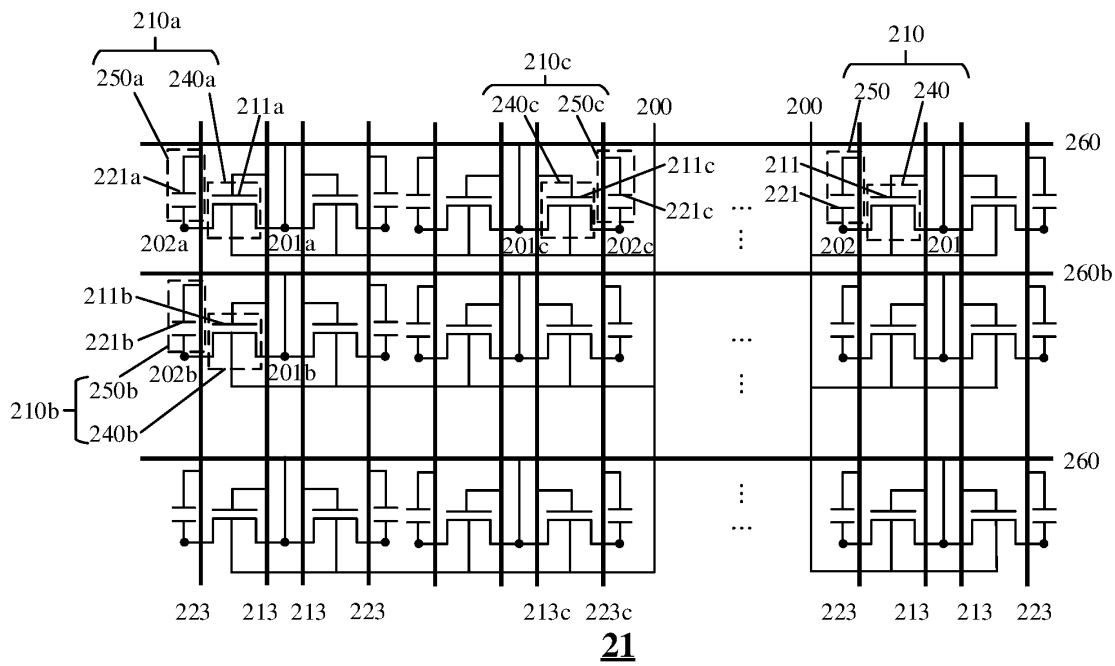


图 8

根据待写入的数据，击穿存储器的反熔丝位结构中的一个目标反熔丝位结构；且保持非目标反熔丝位结构的非击穿状态

S10

图 9